

40V LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction** ٠
- Ideal for Low Power Amplification and Switching .
- Complementary PNP Type Available (DSS5240Y)
- Ultra Small Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363 ٠
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020

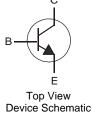
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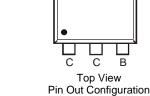
В

- Terminals: Finish Matte Tin annealed over Copper Plated Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

SOT363



Top View



Ordering Information (Note 3)

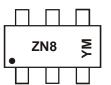
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4240Y-7	ZN8	7	8mm	3,000

Notes:

No purposefully added lead.
Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZN8 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)M = Month (ex: 9 = September)

Date Code Kev

Year	20	10	20	11	20	12	20	13	20	14	20	15
Code	>	<	٢	(Z	<u>Z</u>	I	4	E	3	()
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



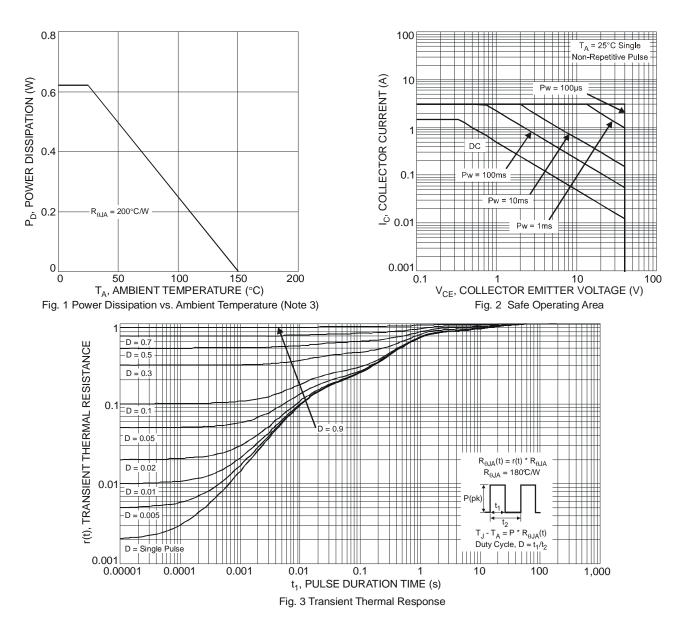
Maximum Ratings $@T_A = 25$ °C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current - Continuous	Ic	2	A
Peak Pulse Collector Current	I _{CM}	3	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^{\circ}C$	PD	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	200	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	۵°

Notes: 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.

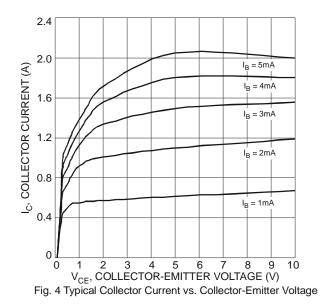


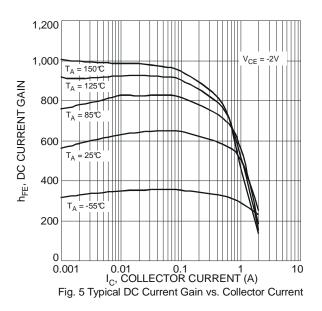


Electrical Characteristics @T_A = 25°C unless otherwise specified

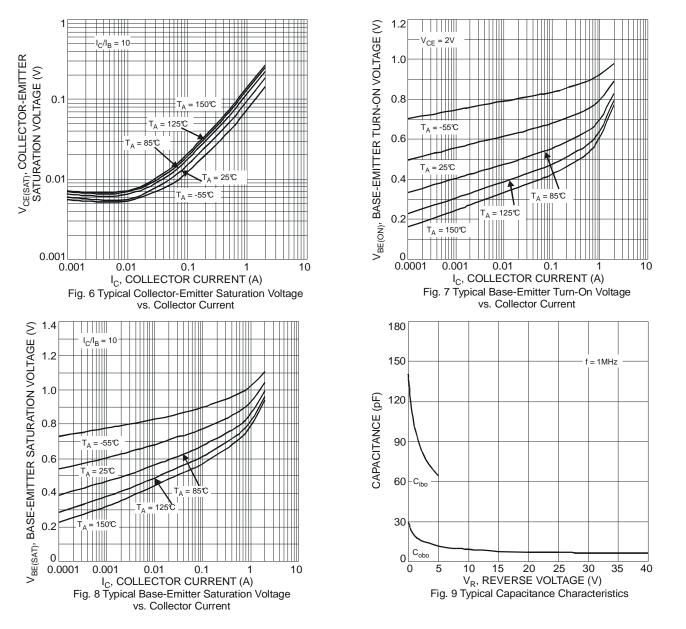
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	150		V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 5)	BVCEO	40	55		V	$I_{C} = 10 mA, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.5		V	$I_{E} = 100 \mu A, I_{C} = 0$
Collector Cutoff Current	I _{CBO}			100	nA	$V_{CB} = 30V, I_E = 0$
			—	50	μΑ	V _{CB} = 30V, I _E = 0, T _A = 150℃
Emitter Cutoff Current	I _{EBO}			100	nA	$V_{EB} = 4V, I_C = 0$
		350	_	_		$V_{CE} = 2V, I_{C} = 100 \text{mA}$
DC Current Gain (Note 5)	h _{FE}	300	—	_		$V_{CE} = 2V, I_{C} = 500 \text{mA}$
	THE	300	—	_	_	$V_{CE} = 2V, I_C = 1A$
		150	—	_		$V_{CE} = 2V, I_C = 2A$
	V _{CE(sat)}	—	45	70		$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 1 {\rm mA}$
		_	52	100		$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}$
Collector-Emitter Saturation Voltage (Note 5)			100	180	mV	I _C = 750mA, I _B = 15mA
			105	180	1	$I_C = 1A$, $I_B = 50mA$
			190	320		$I_{C} = 2A, I_{B} = 200 \text{mA}$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	105	200	mΩ	$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}		—	1.1	V	$I_{C} = 2A, I_{B} = 200 \text{mA}$
Base-Emitter Turn On Voltage	V _{BE(on)}	—		0.75	V	$V_{CE} = 2V, I_{C} = 100 \text{mA}$
Output Capacitance	C _{obo}	_	_	20	рF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	100	250		MHz	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$
Turn-On Time	t _{on}	—	64		ns	
Delay Time	td	_	20	_	ns	
Rise Time	tr		44		ns	$V_{CC} = 10V$
Turn-Off Time	t _{off}		315		ns	$I_{C} = 1A, I_{B1} = -I_{B2} = 50mA$
Storage Time	ts	_	275		ns	
Fall Time	t _f		40		ns	

Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

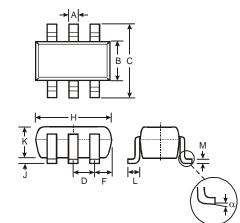








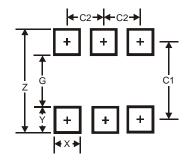
Package Outline Dimensions



SOT363					
Dim	Min	Max			
Α	0.10	0.30			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 Тур				
F	0.40	0.45			
Н	1.80	2.20			
ر	0	0.10			
К	0.90	1.00			
L	0.25	0.40			
Μ	0.10	0.22			
α	0°	8°			
All Dimensions in mm					



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

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